

SILICON BEAM LEAD PIN DIODE

DESCRIPTION:

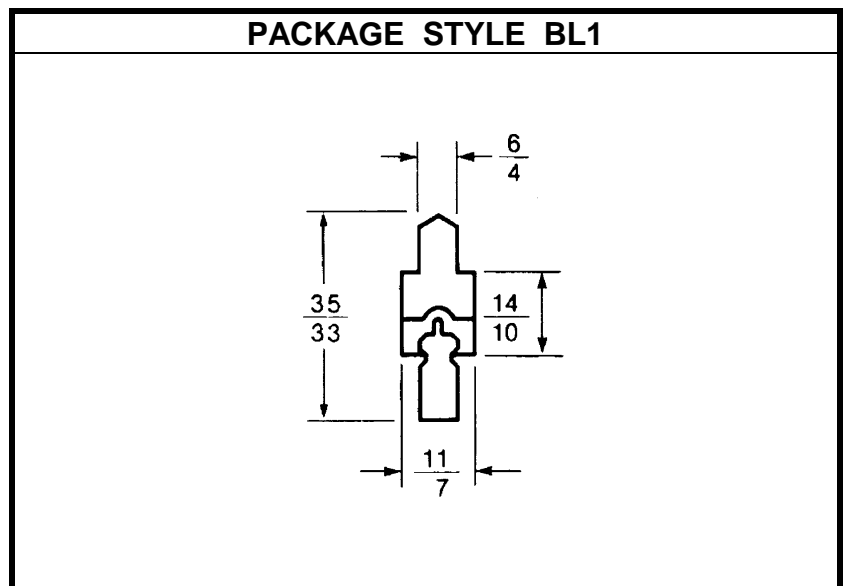
The **ASB8000** is a Silicon Beam Lead PIN Diode Designed for High Speed Switching Applications Up to 18 GHz.

FEATURES INCLUDE:

- **Low Capacitance** - 0.025 pF Typical
- **Low Series Resistance** - 2.5 Ω Typical
- **High Beam Pulls** - 5 Grams Minimum

MAXIMUM RATINGS

I_F	100 mA
V_R	60 V
P_{DISS}	250 mW @ $T_A = 25^\circ\text{C}$
T_J	-65°C to $+175^\circ\text{C}$
T_{STG}	-65°C to $+200^\circ\text{C}$
θ_{JA}	600 $^\circ\text{C/W}$


CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
V_{BR}	$I_R = 10 \mu\text{A}$	60			V
C_J	$V_R = 10 \text{ V}$ $f = 2 - 18 \text{ GHz}$		0.025	0.035	pF
R_S	$I_F = 10 \text{ mA}$ $f = 1.0 \text{ GHz}$		2.5	3.0	Ω
τ	$I_F = 10 \text{ mA}$ $I_R = 6.0 \text{ mA}$		40		nS
t_{rr}	$I_F = 10 \text{ mA}$ $I_R = 6.0 \text{ mA}$		2.4		nS
	Lead Pull	5			gm